



#### 74AVC4T245

### 4-BIT DUAL POWER SUPPLY TRANSLATING BUFFER WITH 3-STATE OUTPUTS

### **Description**

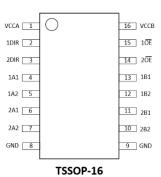
The 74AVC4T245 device is 4-bit, dual supply transceiver that enables bi-directional level translation, designed for asynchronous communication between two data buses. It features four 2-bit inputoutput ports (nAn and nBn), a direction control input (nDIR), an output enable input (nOE) and dual supply pins (VCC(A) and VCC(B)). Both VCC(A) and VCC(B) can be supplied at any voltage between 0.8V and 3.6V, making the device suitable for translating between any of the low voltage nodes (0.8V, 1.2V, 1.5V, 1.8V, 2.5V and 3.3V). Pins nAn, nOE and nDIR are referenced to VCC(A) and pins nBn are referenced to VCC(B). A HIGH on nDIR allows transmission from nAn to nBn and a LOW on nDIR allows transmission from nBn to nAn. The output enable input (nOE) can be used to disable the outputs so the buses are effectively isolated. The device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either VCC(A) or VCC(B) are at GND level, both nAn and nBn are in the highimpedance OFF-state.

The 74AVC4T245 is available in the TSSOP-16 package, and is specified for operation from -40°C to +125°C among all supply voltages. The wide temperature ranges and high ESD tolerance facilitate their use in harsh applications.

#### **Features**

- Supply Voltage Range: VCC(A)/VCC(B): from 0.8V to 3.6V
- Max Data Rates:
  - 380Mbps (1.8V to 3.3V Translation)
  - 200Mbps (<1.8V to 3.3V Translation)
  - 200Mbps (Translate to 2.5V or 1.8V)
  - 150Mbps (Translate to 1.5V)
  - 100Mbps (Translate to 1.2V)
  - 50Mbps (Translate to 0.8V~1.1V)
- High Drive Strength (±12mA at 3.3V)
- IOFF Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
  - Exceeds 8000V Human Body Model (A114)
  - Exceeds 1000V Charged Device Model (C101)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

### **Pin Assignments**



### **Applications**

- Personal electronics
- Industrial
- Enterprise
- Telecom

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



## **Pin Descriptions**

Pin Name	Pin Number	Function
Vcca	1	A port supply Voltage
1DIR	2	Direction Control Pin for Port "1".
2DIR	3	Direction Control Pin for Port "2".
1A1	4	Input/Output 1A1. Referenced to VCCA.
1A2	5	Input/Output 1A2. Referenced to VCCA.
2A1	6	Input/Output 2A1. Referenced to VCCA.
2A2	7	Input/Output 2A2. Referenced to VCCA.
GND	8	Ground
GND	9	Ground
2B2	10	Input/Output 2B2. Referenced to VCCB.
2B1	11	Input/Output 2B1. Referenced to VCCB.
1B2	12	Input/Output 1B2. Referenced to VCCB.
1B1	13	Input/Output 1B1. Referenced to VCCB.
2OE	14	3-state output-mode enable. Pull to High to place port "2" outputs in high-impedance mode. Referenced to VCCA.
1OE	15	3-state output-mode enable. Pull to High to place port "1" outputs in high-impedance mode. Referenced to VCCA.
Vccв	16	B port supply Voltage

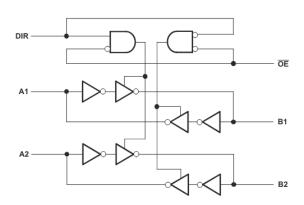
## Function Table (Note 4)

Control F	unctional	Outpu	t Status	
OE	DIR	A Port	B port	Operation
L	L	Enabled	Hi-Z	B to A
L	Н	Hi-Z	Enabled	A to B
Н	X	Hi-Z	Hi-Z	Isolation

Note:

4. Floating input pin is allowed for this case.

## **Logic Diagram**





## Absolute Maximum Ratings (Note 5) (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	7.5	kV
ESD CDM	Charged Device Model ESD Protection	1.5	kV
VCCA, VCCB	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High Impedance or Ioff State	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to Vcco+0.5	V
lıĸ	Input Clamp Current V <sub>I</sub> < 0	-50	mA
Іок	Output Clamp Current	-50	mA
lo	Continuous Output Current	±50	mA
_	Continuous Current Through V <sub>CCA</sub> or GND	±100	mA
TJ	Operating Junction Temperature	+150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Note:

### Recommended Operating Condition (@TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Vcco	Min	Max	Units
$V_{CCA}$	Operating Voltage	<del>_</del>	0.8	3.6	V
Vссв	Operating Voltage	_	0.8	3.6	V
		1.1V	_	-3	
	[	1.4V to 1.6V	_	-6	
Іон	High-Level Output Current  Data Input, nDIR, nOE Input	1.65V to 1.95V	_	-8	mA
	Data Input, IIDIK, IIOL Input	2.3V to 2.7V	_	-9	
		3V to 3.6V	_	-12	
		1.1V	_	3	
		1.4V to 1.6V	_	6	
loL	Low-Level Output Current  Data Input, nDIR, nOE Input	1.65V to 1.95V	_	8	mA
	Data Input, IIDIK, IIOE IIIput	2.3V to 2.7V	_	9	
		3V to 3.6V	_	12	
Vı	Input Voltage		0	3.6	V
\/-	Outsid Mallana	Active State	0	Vcco	V
Vo	Output Voltage	Tri-State	0	3.6	V
TA	Operating Free-Air Temperature		-40	+125	°C

<sup>5.</sup> Stresses greater than those listed under *Absolute Maximum Ratings* can cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to *Absolute Maximum Ratings* for extended periods can affect device reliability.



# $\textbf{Electrical Characteristics} \ \ (\text{Notes 6, 7, 8, 9 \& 10}) \ \ (\underline{\text{@TA}} = +40^{\circ}\text{C to } +125^{\circ}\text{C}, \text{ unless otherwise specified.})$

Compleal	Donomoton	Test	Vccı	Vcco	TA	\= +25	°C	T <sub>A</sub> = -40°C	to +85°C	T <sub>A</sub> = -40°C	to +125°C	Unit
Symbol	Parameter	Condition	VCCI	VCCO	Min	Тур	Max	Min	Max	Min	Max	Unit
			0.8V	_	0.70VCCI	_	_	0.70VCCI	_	0.70VCCI	_	
	High-Level	Data Input,	1.1V to 1.95V	1	0.65VCCI	1	_	0.65VCCI	_	0.65VCCI	1	
VIH	Input Voltage	nDIR, nOE Input	1.95V to 2.7V	1	1.6	1	_	1.6	_	1.6	1	V
			2.7V to 3.6V	ı	2	1	_	2	_	2	1	
			0.8V	_			0.3VCCI		0.3VCCI		0.3VCCI	
	Low-Level	Data Input,	1.1V to 1.95V	ı	_	l	0.35VCCI		0.35VCCI		0.35VCCI	
VIL	Input Voltage	nDIR, nOE Input	1.95V to 2.7V		_	_	0.7	_	0.7	_	0.7	V
			2.7V to 3.6V	_	_	_	0.8	_	0.8	_	0.8	
		I <sub>OH</sub> = -0.1mA	0.8V-3.6V	0.8V- 3.6V	_	_	_	VCCO - 0.1	_	VCCO – 0.1	_	
		I <sub>OH</sub> = -3mA	1.1V	1.1V	0.95	_	_	0.85	_	0.85	_	
Voh	High-Level Output	I <sub>OH</sub> = -6mA	1.4V	1.4V	1.05		_	1.05	_	1.05	_	V
	Voltage	I <sub>OH</sub> = -8mA	1.65V	1.65V	1.2	_	_	1.2	_	1.2	_	
		Іон = -9mA	2.3V	2.3V	1.75	_	_	1.75	_	1.75	_	
		Iон = -12mA	3V	3V	2.3		_	2.3	_	2.3	_	
		I <sub>OL</sub> = 0.1mA	0.8V-3.6V	0.8V- 3.6V	0.1		_	-	0.1		0.1	
		IoL = 3mA	1.1V	1.1V	0.25		_	-	0.25	_	0.27	
Vol	Low-Level Output	IoL = 6mA	1.4V	1.4V	0.35	1	_	1	0.35	1	0.35	V
	Voltage	IoL = 8mA	1.65V	1.65V	0.45	_		_	0.45	_	0.45	
		I <sub>OL</sub> = 9mA	2.3V	2.3V	0.55	_	_	_	0.55	_	0.55	
		IoL = 12mA	3V	3V	0.7	_	_	_	0.7	_	0.7	

Notes:

<sup>6.</sup>  $V_{CCI}$  is the  $V_{CC}$  associated with the input port.

<sup>7.</sup>  $V_{\text{CCO}}$  is the  $V_{\text{CC}}$  associated with the output port.

<sup>8.</sup> All unused data inputs of the device must be held at  $V_{\text{CCI}}$  or GND to ensure proper device operation.

<sup>9.</sup> For  $\overline{\text{OE}}$  values not specified in the data sheet,  $V_{\text{IH}}$  min =  $V_{\text{CCI}} \times 0.7 \text{V}$ ,  $V_{\text{IL}}$  max =  $V_{\text{CCI}} \times 0.3 \text{V}$ . 10. For  $\overline{\text{OE}}$  and DIR  $V_{\text{CCI}}$  values not specified in the data sheet,  $V_{\text{IH}}$  min =  $V_{\text{CCA}} \times 0.7 \text{V}$ ,  $V_{\text{IL}}$  max =  $V_{\text{CCA}} \times 0.3 \text{V}$ .



# 

		Т	est	.,	.,		T <sub>A</sub> = +25	°C	T <sub>A</sub> = -40°C	to +85°C	T <sub>A</sub> = -40°	C to +125°C				
Symbol	Parameter	Con	dition	Vccı	Vcco	Min	Тур	Max	Min	Max	Min	Max	Unit			
lı	Input Current	Vı = Vo GND	cca or	0.8V- 3.6V	0.8V- 3.6V	1	_	±0.25	_	±1	_	±1	μΑ			
1	Off-State	A or B	$V_1$ or $V_0 = 0$	0	0.8V- 3.6V	1	_	±1	_	±3	_	±10	0			
l <sub>OFF</sub>	Current	Port	to 3.6V	0.8V- 3.6V	0		_	±1	_	±3	_	±10	μΑ			
	High-Z State	A or B Port	V <sub>I</sub> or	3.6V	3.6V		_	±1	_	±2	_	±5				
loz	Current	A Port	$V_0 = 0$ to 3.6V	3.6V	0	_	_	±1	_	±2	_	±5	μΑ			
		B Port	10 3.60	0	3.6V	_	_	±1	_	±2	_	±5				
				0.8V- 3.6V	0.8V- 3.6V	_	_	±1	_	±10	_	±35				
Icca	Supply	VI = VC		0.8V- 1.1V	0.8V- 1.1V	_	_	±1	_	±8	_	±25	μΑ			
	Current	ent GND IC	urrent GND IC		GND IO = 0		0-3.6V	0	_	_	±1	_	— ±10 — ±35		±35	
				0	0-3.6V	_	_	±1	_	±1	_	±1				
				0.8V- 3.6V	0.8V- 3.6V		_	±1	_	±10	_	±35				
Іссв	Supply Current	VI = VO		0.8V- 1.1V	0.8V- 1.1V		_	±1	_	±8	_	±25	μΑ			
	Current	GNDIC	<i>J</i> = 0	0-3.6V	0	_	_	±1	_	±1	_	±1				
				0	0-3.6V	_	_	±1	_	±10	_	±35				
ICCA+	Supply Current	VI = VC GND IC		0.8V- 3.6V	0.8V- 3.6V	_	_	±2	_	±20	_	±70	μΑ			
Cı	Control Input Capacitance	nDIR, nOE Input	V <sub>I</sub> = 3.3V or GND	3.3V	_	3.5	_	_	4.5	_	_	4.5	pF			
Со	Input/Output Capacitance	A or B	Vo = 3.3V or GND	3.3V	_	6	_	_	7	_	_	7	pF			

Notes:

- 6.  $V_{\text{CCI}}$  is the  $V_{\text{CC}}$  associated with the input port.
- 7.  $V_{\text{CCO}}$  is the  $V_{\text{CC}}$  associated with the output port.
- 8. All unused data inputs of the device must be held at  $V_{\text{CCI}}$  or GND to ensure proper device operation.
- 9. For  $V_{CCI}$  values not specified in the data sheet,  $V_{IH}$  min =  $V_{CCI} \times 0.7 V$ ,  $V_{IL}$  max =  $V_{CCI} \times 0.3 V$ .
- 10. For  $\overline{\text{OE}}$  and DIR  $V_{\text{CCI}}$  values not specified in the data sheet,  $V_{\text{IH}}$  min =  $V_{\text{CCA}} \times 0.7 \text{V}$ ,  $V_{\text{IL}}$  max =  $V_{\text{CCA}} \times 0.3 \text{V}$ .

## **Package Characteristics**

Symbol	Parameter	Package	Test Condition	Min	Тур	Max	Unit
θЈА	Thermal Resistance Junction-to-Ambient	TSSOP-16	(Note 11)	_	100	_	°C/W
θус	Thermal Resistance Junction-to-Case	TSSOP-16	(Note 11)	_	43	_	°C/W

Note: 11. Test condition for the package type: device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



## Switching Characteristics (@TA = -40°C to +125°C, unless otherwise specified.)

### VCCA = 0.8V

					VCC	В			
Parameter	Test Condition	Direction	0.8V	1.2V ± 0.1V	1.5V ± 0.1V	1.8V ± 0.15V	2.5V ± 0.2V	3.3V ± 0.3V	Unit
			Тур	Тур	Тур	Тур	Тур	Тур	
tpd	Propagation Delay	nAn to nBn	11.0	7.3	6.5	6.2	6.5	7.0	
ιρα	i Topagation Delay	nBn to nAn	11.0	10.0	12.4	12.3	12.1	12.0	
ten	Enable Time	nOE to nAn	18.2	18.2	18.2	18.2	18.2	18.2	ns
ten	Enable Time	nOE to nBn	19.2	12.7	11.4	10.9	10.7	11.1	
tdis	Disable Time	nOE to nAn	14.3	14.3	14.3	14.3	14.3	14.3	
เนเร	Disable Tillle	nOE to nBn	12.6	9.9	9.0	9.4	9.0	9.7	

#### VCCB = 0.8V

					VCC	CA			
Parameter	Test Condition	Direction	0.8V	1.2V ± 0.1V	1.5V ± 0.1V	1.8V ± 0.15V	2.5V ± 0.2V	3.3V ± 0.3V	Unit
			Тур	Тур	Тур	Тур	Тур	Тур	
to d	Decrease the Delevi	nAn to nBn	14.5	12.7	12.4	12.3	12.1	12.0	
tpd	Propagation Delay	nBn to nAn	14.5	7.3	6.5	6.2	5.9	6.0	
ton	Enable Time	nOE to nAn	18.2	13.0	12.1	9.6	7.3	6.4	
ten	Enable Time	nOE to nBn	19.2	15.8	15.3	15.0	15.0	14.8	ns
tdis	Disable Time	nOE to nAn	14.3	9.6	8.5	7.5	7.7	8.6	
idis	Disable Tillle	nOE to nBn	17.0	13.8	13.4	13.1	12.9	12.7	



## Switching Characteristics (@TA = -40°C to +125°C, unless otherwise specified.) (continued)

### $V_{CCA} = 1.2V \pm 0.1V$

										Vссв								
Parameter	Test Conditions	Direction	1.2	2V ± 0.	1V	1.5V ± 0.1V		1.8V ± 0.15V		2.5	5V ± 0.	2V	3.3V ± 0.3V			Unit		
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
to d	Propagation	nAn to nBn	0.5	3	8.3	0.5	2.9	6.3	0.5	2.1	5.5	0.5	2.1	4.6	0.5	2.3	4.6	
tpd Delay	nBn to nAn	0.5	3	8.3	0.5	3.1	7.8	0.5	2.8	7.7	0.5	2.1	7.4	0.5	2.2	7.3		
ton	Enable Time	nOE to nAn	1.8	3.9	11.7	1.8	4.2	11.7	1.8	4.3	11.7	1.8	3.5	11.7	1.8	3.5	11.7	20
ten	Enable fille	nOE to nBn	1.9	4	13.0	1.9	2.5	9.5	1.9	3.3	8.2	1.4	3.6	7.9	1.2	4.5	7.7	ns
tdis	Disable Time	nOE to nAn	1.4	3.2	11.5	1.4	2.3	11.5	1.4	3	11.5	1.4	3	11.5	1.4	3.1	11.5	
เนเร	DISADIE TIME	nOE to nBn	1.1	3	10.0	1.1	2.2	8.1	1.1	2.9	7.5	1.0	2.5	6.3	1.0	5.5	6.3	

#### $V_{CCA} = 1.5V \pm 0.1V$

							Vo	СВ					
Parameter	Test Conditions	Direction	1.2V ± 0.1 V		1.5V ± 0.1V		1.8V ± 0.15V		2.5V ± 0.2V		3.3V ± 0.3V		Unit
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
tnd	Propagation	nAn to nBn	0.3	7.8	0.3	6.3	0.3	5.2	0.4	4.2	0.4	4.2	
tpd Delay	nBn to nAn	0.7	6.3	0.7	6.3	0.5	5.9	0.4	5.7	0.3	5.6		
ton	Enable Time	nOE to nAn	1.8	10.5	1.4	9.6	1.1	9.5	0.7	9.7	0.4	9.4	
ten	Enable Time	nOE to nBn	1.9	11.0	1.4	9.6	1.1	7.7	0.9	7.1	0.9	6.9	ns
tdia	Disable Time	nOE to nAn	1.1	10.2	1.8	10.2	1.5	10.2	1.3	10.2	1.6	10.2	
tdis Disable Time		nOE to nBn	1.4	10.4	1.9	10.3	1.9	9.1	1.4	7.4	1.2	7.6	

#### $V_{CCA} = 1.8V \pm 0.15V$

	_						Vc	СВ					
Parameter	Test Conditions	Direction	1.2V ± 0.1V		1.5V ± 0.1V		1.8V ± 0.15V		2.5V ± 0.2V		3.3V ± 0.3 V		Unit
	Conditions		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
4	Propagation	nAn to nBn	0.1	7.7	0.1	5.9	0.1	4.9	0.1	3.9	0.3	3.9	
tpd	Delay	nBn to nAn	0.6	5.5	0.6	5.3	0.5	4.9	0.3	4.6	0.3	4.5	
ton	Enable Time	nOE to nAn	1.8	9.0	1	8.6	1	7.3	0.6	7.3	0.4	7.2	
ten	Enable Time	nOE to nBn	1.7	10.5	1.2	9.2	1	7.4	0.8	6.7	8.0	6.5	ns
tdia	Disable Time	nOE to nAn	1.0	8.9	1.6	8.6	1.8	8.7	1.3	8.7	1.6	8.7	
tdis	Disable Time	nOE to nBn	1.2	10.0	1.7	9.9	1.6	8.7	1.2	7.4	1	6.9	



## Switching Characteristics (@TA = -40°C to +125°C, unless otherwise specified.) (continued)

### $V_{CCA} = 2.5V \pm 0.2V$

			Vccв										
Parameter	Test Conditions	Direction	1.2V ± 0.1V		1.5V =	5V ± 0.1V 1.8V ± 0.15		0.15V	2.5V ± 0.2V		3.3V ± 0.3V		Unit
Condition			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
to d	Propagation	nAn to nBn	0.1	7.4	0.1	5.7	0.1	4.6	0.2	3.9	0.1	3.6	
tpd	Delay	nBn to nAn	0.6	4.6	0.6	4.2	0.4	4.1	0.2	3.9	0.2	3.3	
400	Enable Time	nOE to nAn	1.0	8.0	0.7	6.7	0.7	6.5	0.6	5.9	0.4	4.8	
ten	Enable Time	nOE to nBn	1.5	9.8	0.9	8.8	0.8	7.0	0.6	5.8	0.6	4	ns
tdis Disable Lime	nOE to nAn	0.7	9.0	1	8.4	1	8.4	1	6.2	1	6.6		
	nOE to nBn	0.9	9.9	1.5	9.4	1.3	8.2	1.1	6.2	0.9	5.2		

#### $V_{CCA} = 3.3V \pm 0.3V$

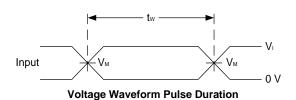
		Test Conditions Direction	Vccв										
Parameter			1.2V ± 0.1V		1.5V :	± 0.1V	1.8V ± 0.15V 2.5V ± 0.2V 3.3V ± 0		± 0.3V	Unit			
	Conditions		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
tod	Propagation	nAn to nBn	0.1	7.3	0.1	5.6	0.1	4.5	0.1	3.7	0.1	2.9	
tpd	Delay	nBn to nAn	0.6	4.6	0.6	4.2	0.4	3.9	0.2	3.7	0.1	2.8	
ton	Enable Time	nOE to nAn	0.7	9.2	0.6	8.7	0.6	5.9	0.6	5.6	0.4	3.8	
ten	Enable Time	nOE to nBn	1.4	9.5	0.8	8.7	0.6	6.8	0.5	5.7	0.5	3.8	ns
Adia Diaghla Tina	nOE to nAn	0.6	9.5	0.7	9.3	0.7	8.3	0.7	5.6	0.7	6.6		
เดเร	tdis Disable Time	nOE to nBn	0.8	9.5	1.4	9.3	1.2	8.1	1	6.4	0.8	6.2	

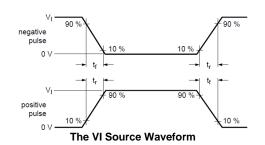
### Operating Characteristics (@TA = +25°C, unless otherwise specified.)

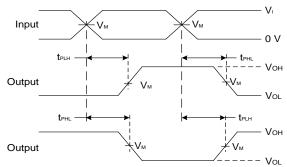
Parameter	Test Condition		0.8V	1.2V	1.5V	1.8V	2.5V	3.3V	Unit	
	A to B	Enabled	CL = 0,	0.2	0.2	0.2	0.2	0.3	0.4	
CpdA	7100	Disabled	RL = Open, f = 10MHz,	0.2	0.2	0.2	0.2	0.3	0.4	
,	R to A	B to A Enabled  Disabled	tr = tf = 1ns, VCCA = VCCB	9.5	9.7	9.8	9.9	10.7	11.9	
	BIOA			0.6	0.6	0.6	0.6	0.7	0.7	
	A to B	Enabled	9.5	9.7	9.8	9.9	10.7	11.9	pF	
CpdB	Alob	Disabled	CL = 0, RL = Open, f = 10MHz,	0.6	0.6	0.6	0.6	0.7	0.7	
Орав	B to A	Enabled	t = 10MHZ, tr = tf = 1ns, VCCA = VCCB	0.2	0.2	0.2	0.2	0.3	0.4	
		Disabled		0.2	0.2	0.2	0.2	0.3	0.4	



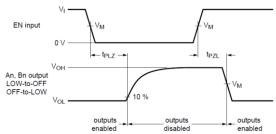
### **Parameter Measurement Information**







Voltage Waveform Propagation Delay Times Inverting and Non-Inverting Outputs



The Enable/Disable (EN) to Output (Yn) Times

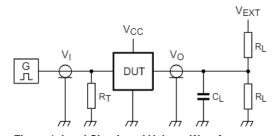


Figure 1. Load Circuit and Voltage Waveforms

Parameter	S1
tpd	Open
ten/tdis	2*VCCO
ten/tdis	GND

vcc	RL	CL	VTP
0.8V-1.6V	2kΩ	15pF	0.1V
1.65V-2.7V	2kΩ	15pF	0.15V
3.0V-3.6V	2kΩ	15pF	0.3V

Notes: A. Includes test lead and test apparatus capacitance.

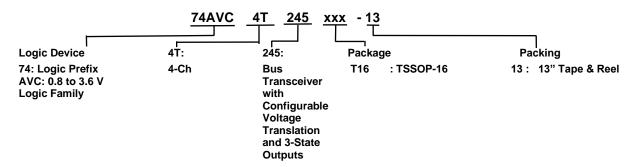
B. f = 1MHz,  $\Delta t/\Delta V$  < 1ns/V.

C.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD}$ .

D.  $t_r$ ,  $t_f < 1$ ns.



### Ordering Information (Notes 12, 13, 14)



Orderable Part Number	Packago Codo	Bookogo	Packing			
Orderable Part Nulliber	Package Code	Package	Qty.	Carrier		
74AVC4T245T16-13	T16	TSSOP-16	2,500	13" Tape & Reel		

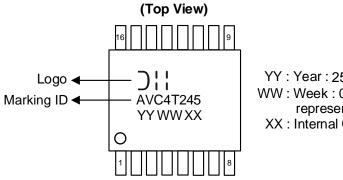
Notes: 12. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

13. Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html.

14. The taping orientation is located on our website at https://www.diodes.com/assets/Packaging-Support-Docs/AP02007.pdf.

### **Marking Information**

#### TSSOP-16



YY: Year: 25, 26, 27~ WW: Week: 01~52; 52

represents 52 and 53 week

XX: Internal Code

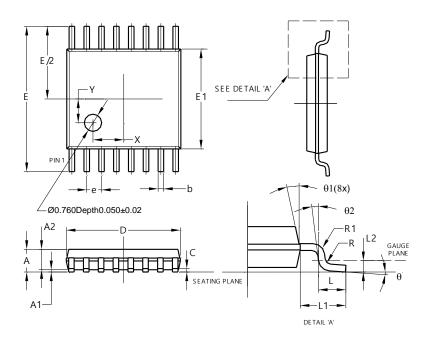
Orderable Part Number	Package	Marking ID
74AVC4T245T16-13	TSSOP-16	AVC4T245



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TSSOP-16

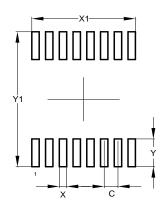


TSSOP-16					
Dim	Min	Max	Тур		
Α	•	1.08	-		
A1	0.05	0.15	-		
A2	0.80	0.93	-		
b	0.19	0.30	-		
C	0.09	0.20	-		
D	4.90	5.10	-		
Е	6.40 BSC				
E1	4.30	4.50	-		
е	0.65 BSC				
L	0.45	0.75	-		
L1	1	.00 RE	F		
L2		).25 BS	С		
R / R1	0.09	-	-		
X	•	-	1.350		
Υ	-	-	1.050		
θ	0°	8°	-		
θ1	5°	15°	-		
θ2	0°	-	-		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSSOP-16



Dimensions	Value
Dilliensions	(in mm)
С	0.650
Х	0.350
X1	4.900
Υ	1.400
Y1	6.800

### **Mechanical Data**

#### TSSOP-16

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Mate Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.055 grams (Approximate)



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